

**REMARKS**

As a preliminary matter, Applicant's representative would like to thank the Examiner for courtesies extended in the personal interview conducted on September 19, 2005.

An Examiner's Interview Summary Record (PTOL-413) was provided by the Examiner at the interview on September 19, 2005.

Applicant submits this Statement to comply with the requirements of M.P.E.P. § 713.04.

In the interview, the following was discussed:

**A. Identification of claims discussed:**

Claims 1 and 20.

**B. Identification of prior art discussed:**

IBM Publication NN75101486.

**C. Identification of principal proposed amendments:**

1. (Currently Amended) A method of producing a crystal growth substrate, comprising:  
molding a seed substrate into a desired shape so that irregularities are provided to a sapphire growth surface of said seed substrate;  
growing a sapphire crystal on said sapphire growth surface of said seed substrate to thereby form a sapphire substrate; and  
removing said seed substrate selectively from said sapphire substrate formed by said growing a sapphire crystal,

wherein cavities are formed periodically in said sapphire growth surface of said seed substrate during said molding a seed substrate.

20. (Currently Amended) A method of producing a semiconductor light-emitting element, comprising:

growing a desired semiconductor layer as a crystal on a sapphire substrate grown on a seed substrate; and

removing said seed substrate,

wherein cavities are formed periodically in a sapphire growth substrate of said seed substrate.

**D. Brief Identification of principal arguments:**

Applicant's representative respectfully pointed out that the claimed invention (e.g., as defined in claims 1 and 20) is directed to a method of producing a crystal growth substrate wherein cavities are formed periodically in the sapphire growth surface of the seed substrate during the molding a seed substrate (e.g., see Application at page 11, lines 21-24). These features are important for improving the external quantum efficiency of a semiconductor light-emitting element, as well as light-condensing characteristics and light directivity (see Application at page 3, lines 9-15).

Applicant's representative further pointed out that the IBM references did not teach or suggest each and every feature of the claimed invention, including cavities formed periodically in

the sapphire growth surface of the seed substrate during the molding a seed substrate.

**E. Results of the Interview:**

In response to the arguments presented, the Examiner indicated that the limitation argued above was not taught or suggested by the IBM reference. However, the Examiner stated that a new search would be conducted in light of Applicant's arguments.

**F. Conclusion:**

Applicant respectfully submits that the IBM does not teach or suggest each and every element of the claimed invention.

Thus, the Examiner is respectfully requested to pass the above application to issue at the earliest possible time.

Serial No. 10/628,492  
Docket No. T36-157944M/RS

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The Commissioner is hereby authorized to charge any fees or to credit any overpayment in fees to Assignee's Deposit Account No. 50-0510.

Respectfully Submitted,

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